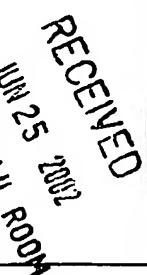
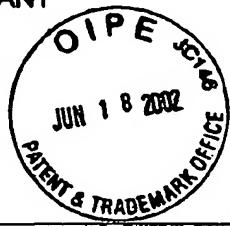


Form PTO-1449		Atty. Docket No. 98095DIV4	Serial No.: 10/008,653
U. S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE			
INFORMATION DISCLOSURE STATEMENT BY APPLICANT			
(Use several sheets if necessary)		Applicant Gonzales	
		Filing Date November 9, 2001	Group 2815



U. S. PATENT DOCUMENTS

Examiner Initial	Document Number	Issue Date	Patentee	Class	Sub-Class	Filing Date
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Examiner Initial	Document Number	Public. Date	County or Patent Office	Class	Sub-Class	Transl Y N

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KL			Wolf et al. (Silicon Processing For The VLSI ERA, Volume 1: Process Technology, pp. 397-399, 1986)
EXAMINER: Initial citation considered. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.			

Form PTO-1449		Atty. Docket No. 98095DIV3	Serial No. 10/008,653
<p>U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE</p> <p>INFORMATION DISCLOSURE STATEMENT BY APPLICANT</p> <p>(Use several sheets if necessary)</p>			
<p>Applicant Gonzalez et al.</p>			
Filing Date 11/9/01		Group <i>2815</i>	

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